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Article

Structure-Optimized Photonic Phase-Change Memory Achieving High Storage Density and Endurance Towards Reconfigurable Telecommunication Systems

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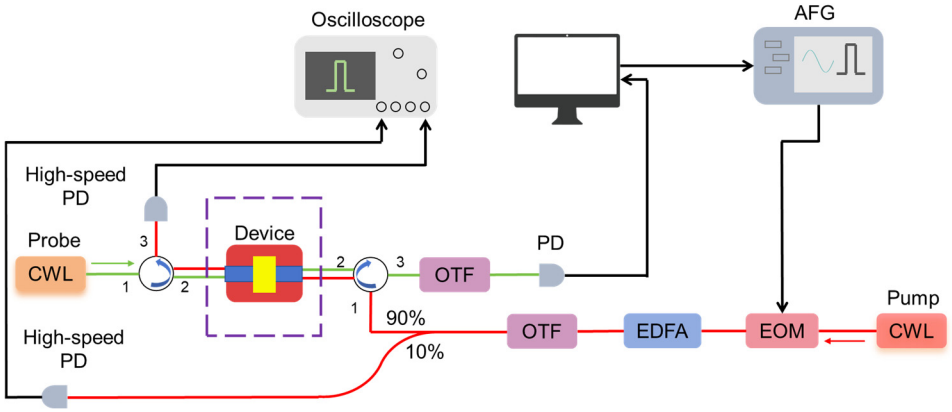


Figure S1. Optical measurement scheme. CWL: continuous wave laser; OTF: optical tunable filter; EDFA: erbium-doped fiber amplifier; EOM: electro-optical modulator; PD: photodetector/receiver; AFG: arbitrary function generator.

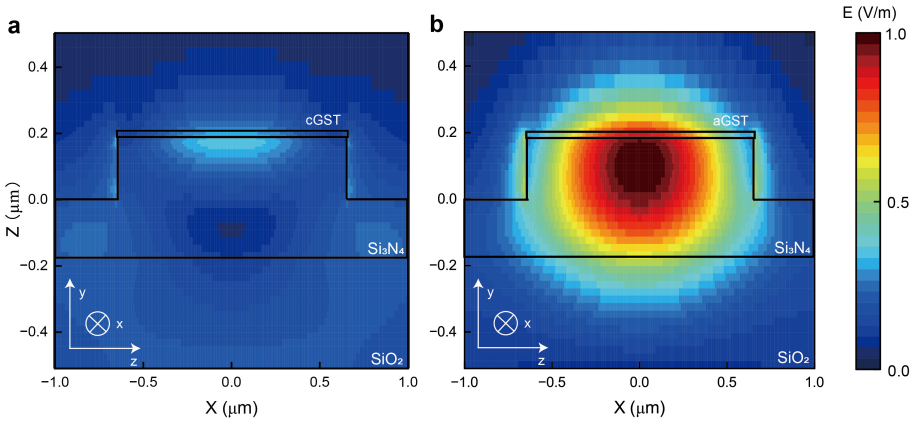


Figure S2. The optical mode profiles of photonic phase-change memory in the crystalline (**a**) and amorphous (**b**) states.

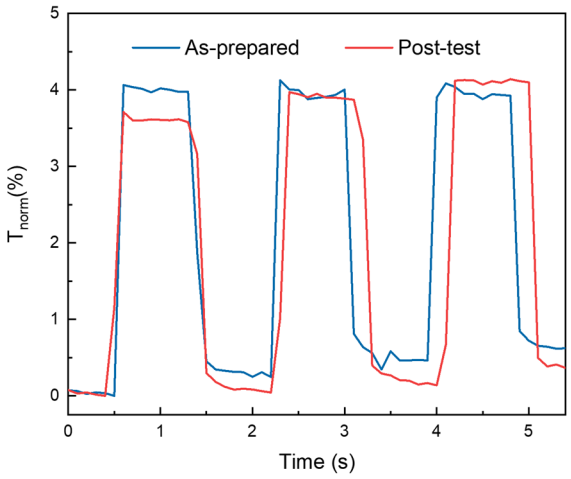


Figure S3. Switching stability between different transmission states measured before and after the retention characteristics test in Figure 2b.

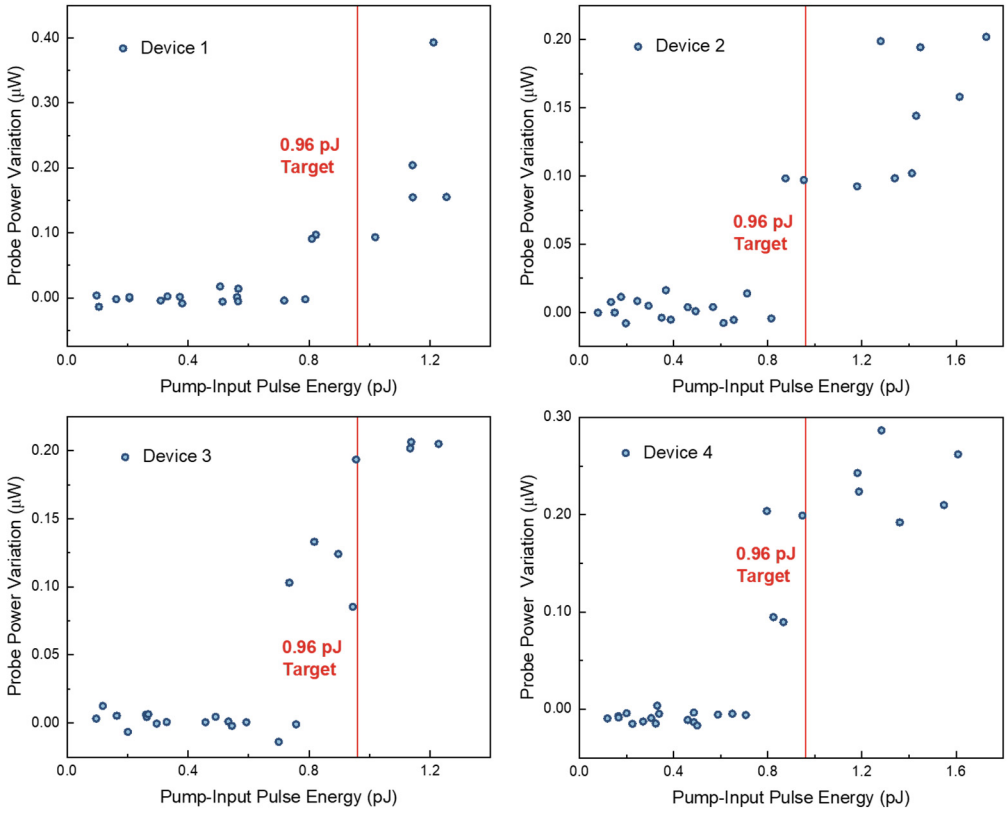


Figure S4. Transmission modulation characteristics from four additional devices: probe power variation versus programming pulse energy during the amorphization process from four additional devices.